

1.

$$fan-out = \text{minimum of } \left(\frac{I_{OH}}{I_{IH}}, \frac{I_{OL}}{I_{IL}} \right)$$

$$= \text{minimum of } \left(\frac{1mA}{0.05mA}, \frac{20mA}{2mA} \right)$$

$$= \text{minimum of } (20, 10) = 10$$

$$\text{power dissipation} = V_{CC} \cdot \left(\frac{I_{CCH} + I_{CCL}}{2} \right) / 4$$

$$= 5V \cdot \left(\frac{10 + 20}{2} \right) \cdot \frac{1}{4}$$

$$= 5 \cdot 15 \cdot \frac{1}{4} = \frac{75}{4} = 18.75mW$$

$$\text{propagation delay} = \text{maximum of } (t_{PLH} \text{ or } t_{PHL})$$

$$= \text{maximum of } (3ns, 3ns) = 3ns$$

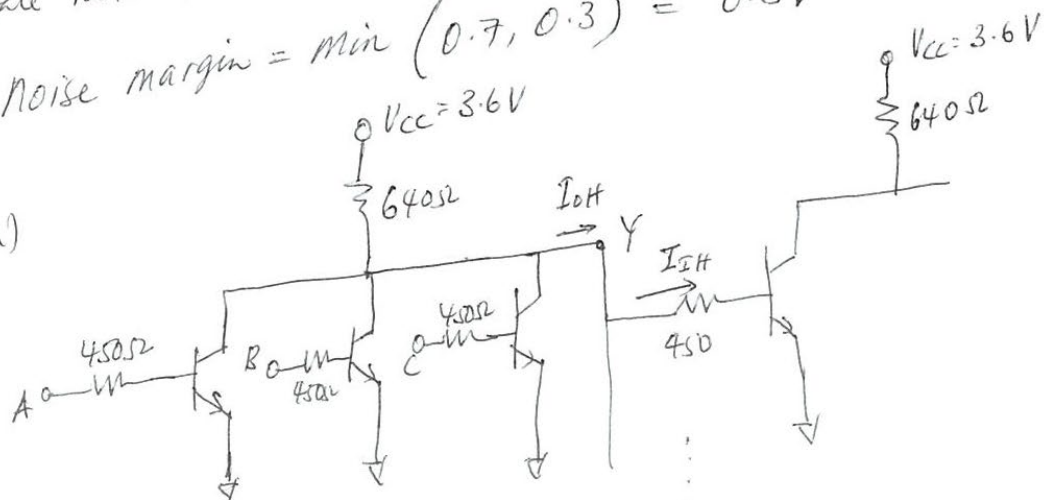
$$\text{High state Noise margin} = V_{OH} - V_{IH} = 2.7V - 2V = 0.7V$$

$$\text{Low state noise margin} = V_{IL} - V_{OL} = 0.8 - 0.5 = 0.3V$$

$$\text{Noise margin} = \min(0.7, 0.3) = 0.3V$$

2.

(a)



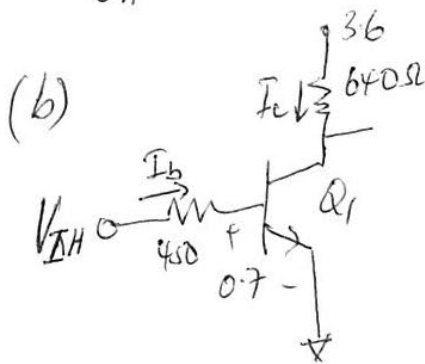
For high output, all inputs (A, B, C) ~~are to~~ should be low and all the transistors are off. Hence, I_{OH} flows through only 640Ω from the supply $V_{CC}=3.6V$.

$$3.6V = 640 I_{OH} + 450 \frac{I_{OH}}{5} + 0.7$$

$$= (640 + 90) I_{OH} = 2.9$$

$$I_{OH} = \frac{2.9}{730} = \underline{\underline{3.9mA}}$$

$$V_{OH} = V = 3.6 - 640(3.9) = \underline{\underline{1.06V}}$$



When Q goes into saturation $V_{CE} \approx 0.2$

$$\therefore I_C = \frac{3.6 - 0.2}{640} A = 5.31mA$$

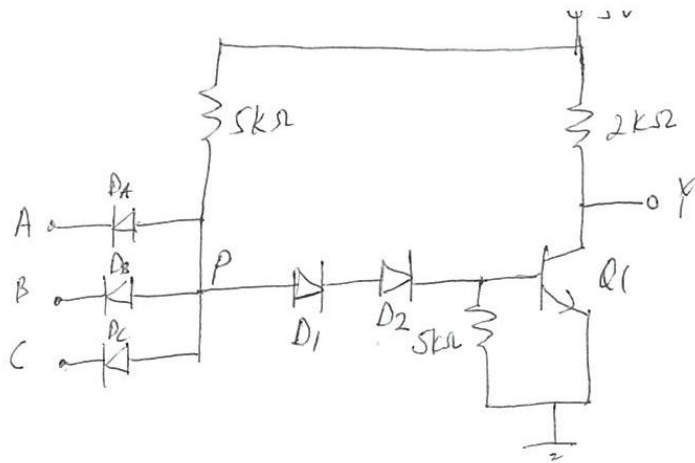
$$I_B = \frac{I_C}{20} = 0.26mA$$

$$V_{IH} = 450 \times I_B + 0.7 = 0.82V$$

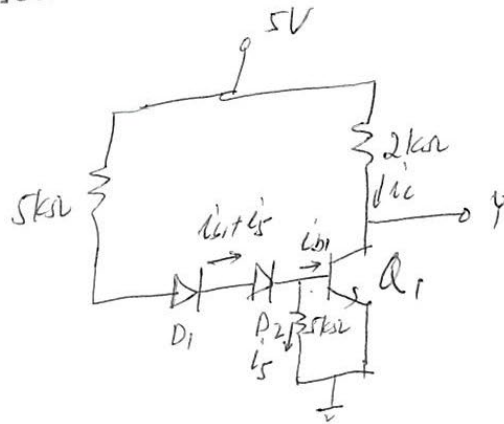
(c) $V_{OH} - V_{IH} = \text{noise margin}$

$$\text{noise margin} = 1.06 - 0.82 = 0.24V$$

3.



When A, B, and C are high, ~~the~~ diode D_A , D_B and D_C will be reversed biased and the above circuit can be represented as



$$5V - 5(I_{B1} + I_S) - 0.7 - 0.7 - 0.7 = 0$$

$$5 - 5(I_{B1} + I_S) = 2.1$$

$$I_{B1} + I_S = \frac{5 - 2.1}{5} = 0.58 \text{ mA}$$

$$I_S = \frac{0.7}{5} = 0.14 \text{ mA}$$

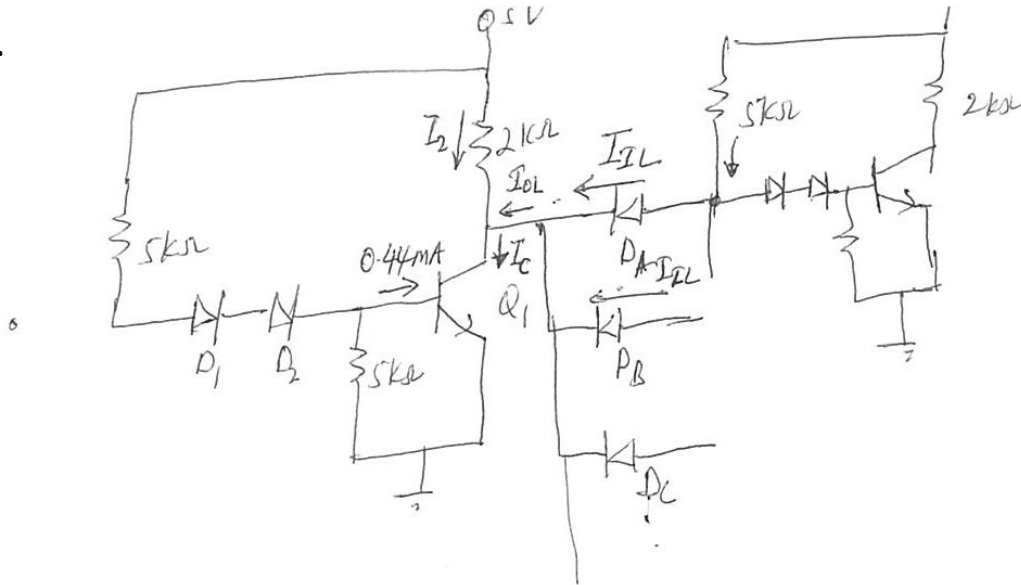
$$\therefore I_{B1} = 0.58 - 0.14 = 0.44 \text{ mA}$$

$$\text{for } h_{FE} = 20, \quad I_{CS} = 20(0.44) = 8.8 \text{ mA}$$

$$I_{CS} = \frac{5 - 0.2}{2} = 2.4 \text{ mA} < 8.8 \text{ mA}$$

$\therefore Q_1$ is in saturation

4.



$$I_C = 0.44 \times 20 = 8.8 \text{ mA}$$

$$(a) \quad I_2 = \frac{5 - 0.2}{2} = 2.4 \text{ mA}$$

$$I_{OL} = 8.8 \text{ mA} - 2.4 \text{ mA} = 6.4 \text{ mA}$$

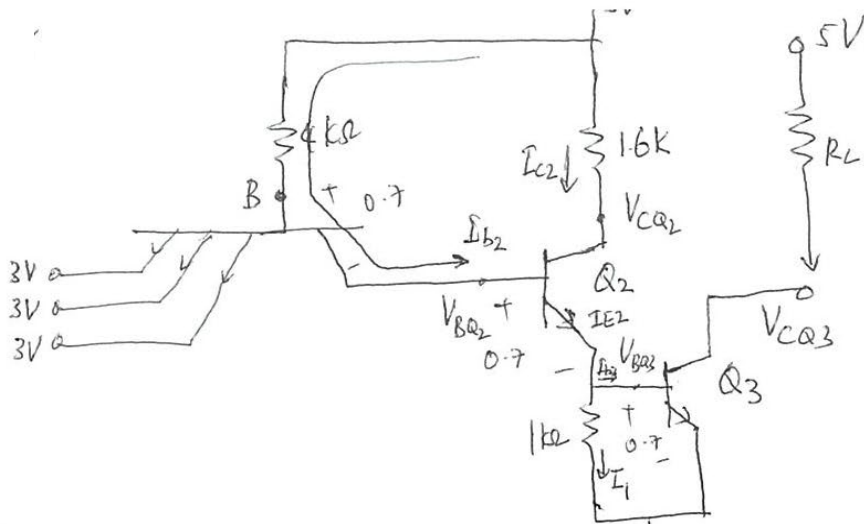
$$(b) \quad I_5 = \frac{5 - 0.9}{5} = 0.82 \text{ mA} = I_{IL}$$

$$(c) \quad 2.4 + 0.82 \text{ N}$$

$$(d) \quad N = \frac{I_{OL}}{I_{IL}} = \frac{6.4 \text{ mA}}{0.82 \text{ mA}} = 7.8$$

$$(e) \quad \underline{\underline{N = 7}}$$

5.



(a)

$$V_{BE1} = 2.1V \quad V_{CE2} = 0.2 + 0.7 = 0.9V$$

$$V_{BE2} = 1.4V \quad V_{CE3} = 0.2V$$

$$V_{BE3} = 0.7V \quad V_{E2} = V_{BE3} = 0.7V$$

(b)
$$I_{B2} = \frac{5 - 2.1}{4} = 0.725mA$$

$$I_{C2} = \frac{5 - 0.9}{1.6} = 2.5625mA$$

(c)
$$h_{fe} = \frac{2.5625}{0.725} = 3.53$$

(c)
$$I_{B3} = I_{E2} - I_1 = (I_{B2} + I_{C2}) - I_1$$

$$= [(0.725 + 2.5625) - 0.7]$$

$$= 2.5875$$

(d)
$$I_{C3} = 2.5875 \times 6.18 = 16mA$$

(e)
$$R_L = \frac{5 - 0.2}{16} = 300\Omega$$

6. (a) When C is low and A is low

Q_7 is off	Q_2 is off	Q_5 is ON
Q_6 is off	Q_3 is off	Q_4 is ON

Y is high

(b) When C is low and A is high

Q_7 is off	Q_2 is ON	Q_4 is ON OFF
Q_6 is off	Q_3 is ON	Q_5 is ON off

Q_7 is ON Q_2 is ON Q_4 is off

Q_6 is ON Q_3 is off

Y is high impedance

7. By analyzing the PDN, the function is:

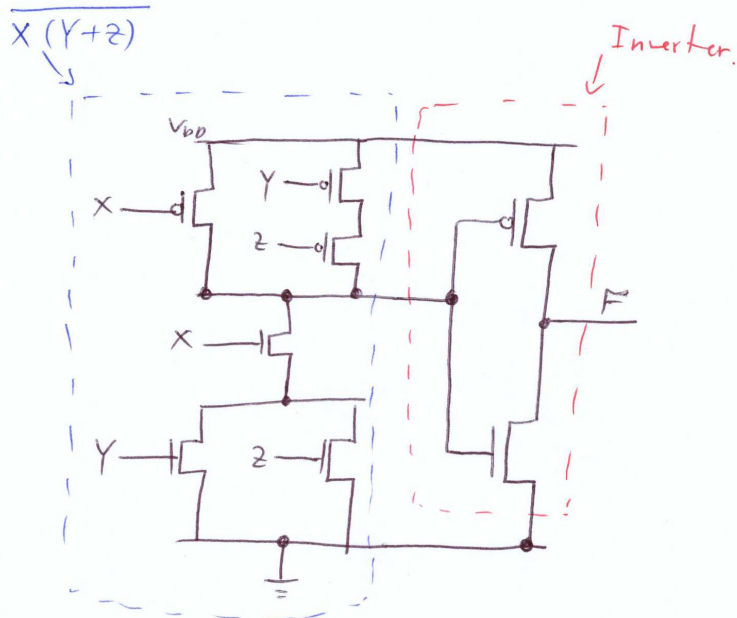
$$Z = \overline{AB + C + D}$$

$$= (\overline{A} + \overline{B}) \overline{C} \overline{D}$$

8.

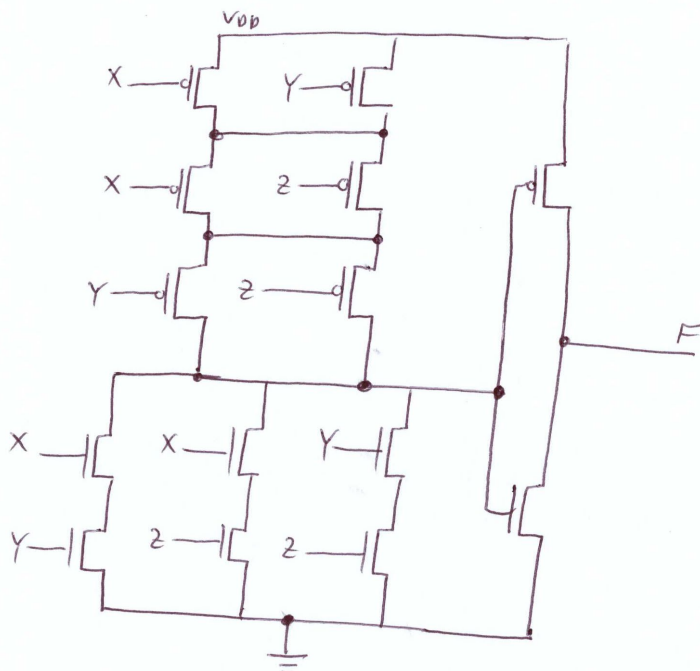
a. To minimize the number of transistors used, factorize the function:

$$F = X(Y+Z)$$

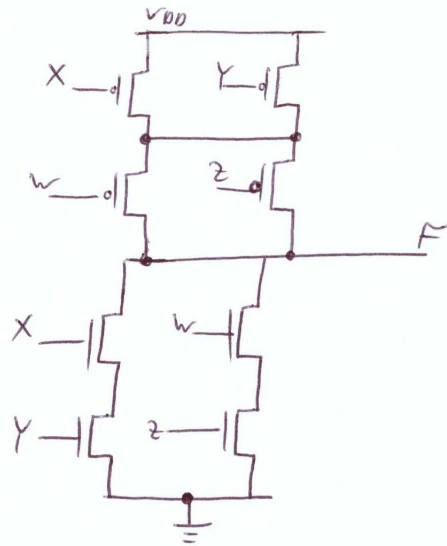


b. (This function may be minimized further)

$$F = XY + XZ + YZ$$

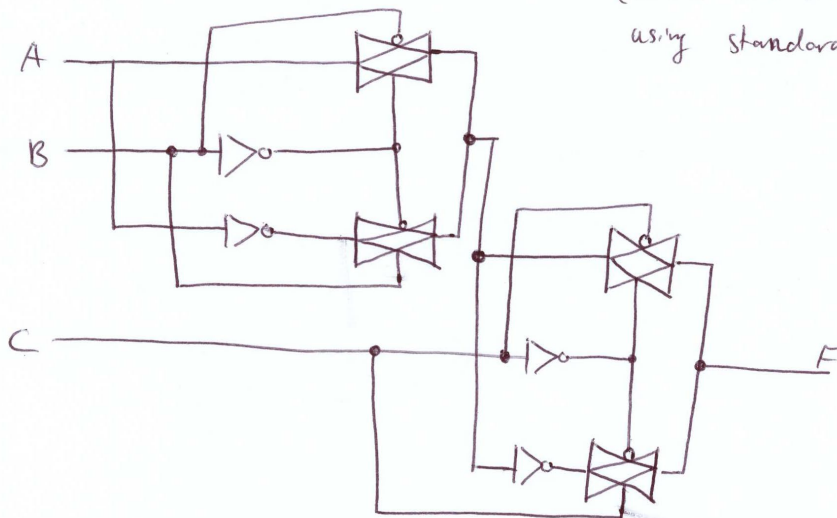


c. $F = \overline{XY + wz}$



d. Using transmission gates:

(where the inverters are implemented using standard CMOS design).

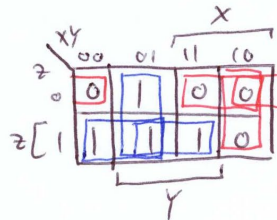


9. a.

$$F = YZ + \bar{X}Z + \bar{X}Y\bar{Z}$$

Implementing this directly requires 20 transistors.

Using a k-map, try to find minimal expression for both F and \bar{F} to check which one gives the least transistors.



$$F = \bar{X}Z + YZ + \bar{X}Y \quad (16)$$

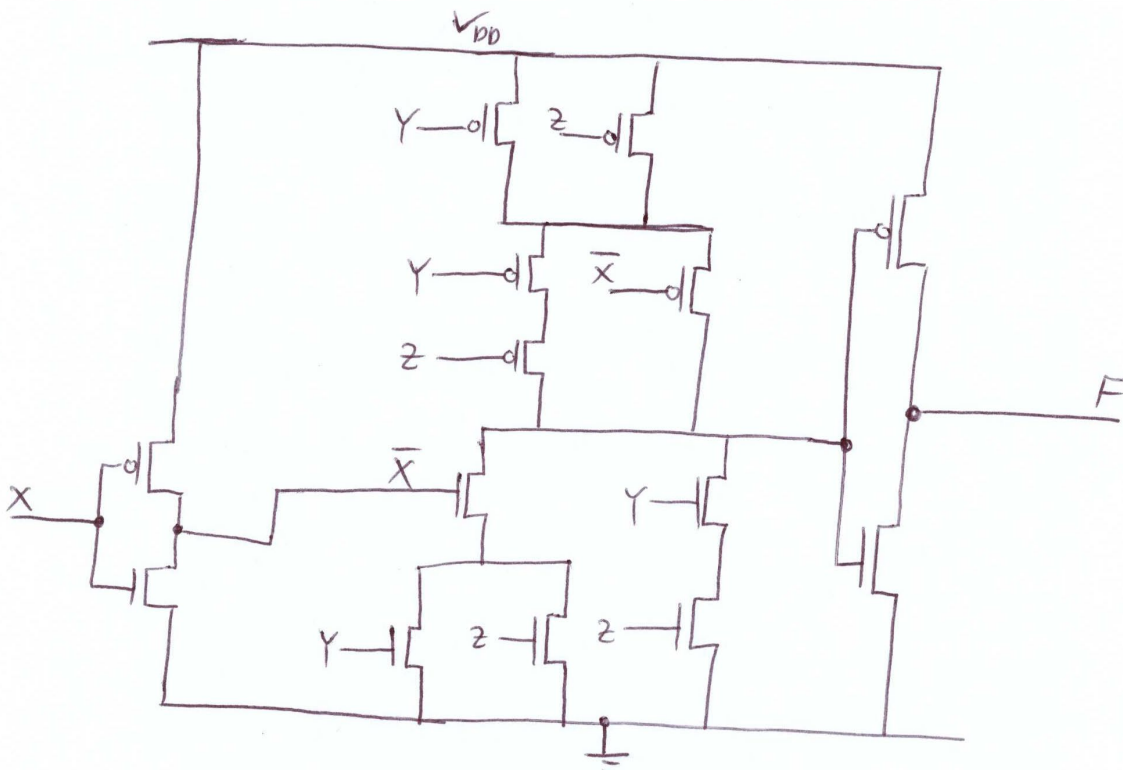
$$= \bar{X}(Y+Z) + YZ \quad (14)$$

$$\bar{F} = X\bar{Y} + X\bar{Z} + \bar{Y}\bar{Z} \quad (16)$$

$$= X(\bar{Y} + \bar{Z}) + \bar{Y}\bar{Z} \quad (14)$$

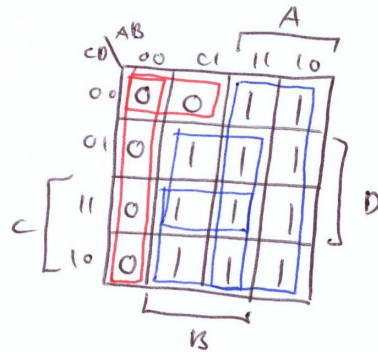
can implement either one

Implement: $F = \bar{X}(Y+Z) + YZ$



b. use K-map to simplify the function:

$$F = A\bar{D} + A\bar{B} + BD + BC \quad (22 \text{ transistors})$$



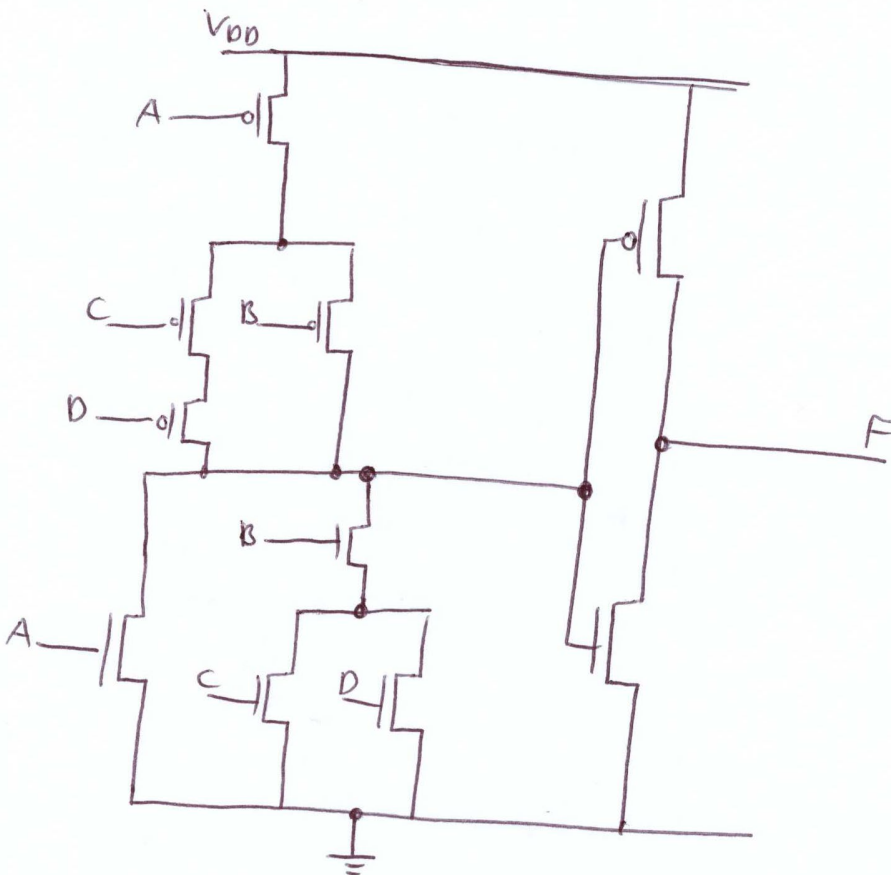
$$F = A + BC + BD \quad (12)$$

$$= A + B(C + D) \quad (10)$$

$$\bar{F} = \bar{A}\bar{B} + \bar{A}\bar{C}\bar{D} \quad (18)$$

$$= \bar{A}(\bar{B} + \bar{C}\bar{D}) \quad (16)$$

So implement $F = A + B(C + D)$



10.

a. Try to minimize number of transistors:

$$F = (A + \bar{C})(\bar{A} + C)(B + \bar{D})(\bar{B} + D) \quad (26)$$

$$= (AC + \bar{A}\bar{C})(BD + \bar{B}\bar{D}) \quad (26)$$

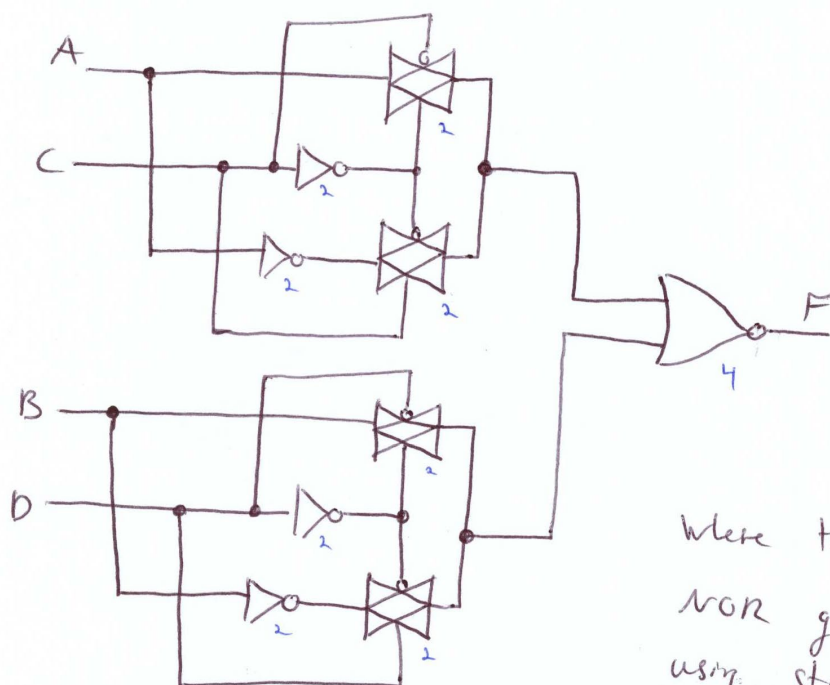
$$= \overline{(A \oplus C)(B \oplus D)} \quad (22)$$

using TG's.

$$= \overline{(A \oplus C) + (B \oplus D)} \quad (20)$$

using TG's

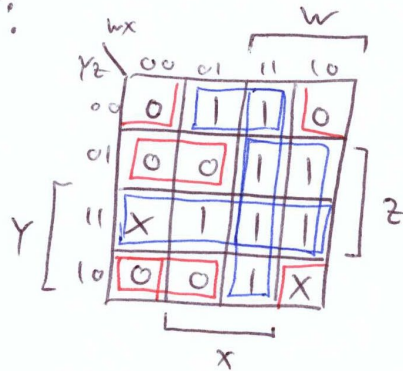
So implement: $F = \overline{(A \oplus C) + (B \oplus D)}$



(20)

where the inverters and the NOR gate are implemented using standard CMOS.

b. Find an expression for F :



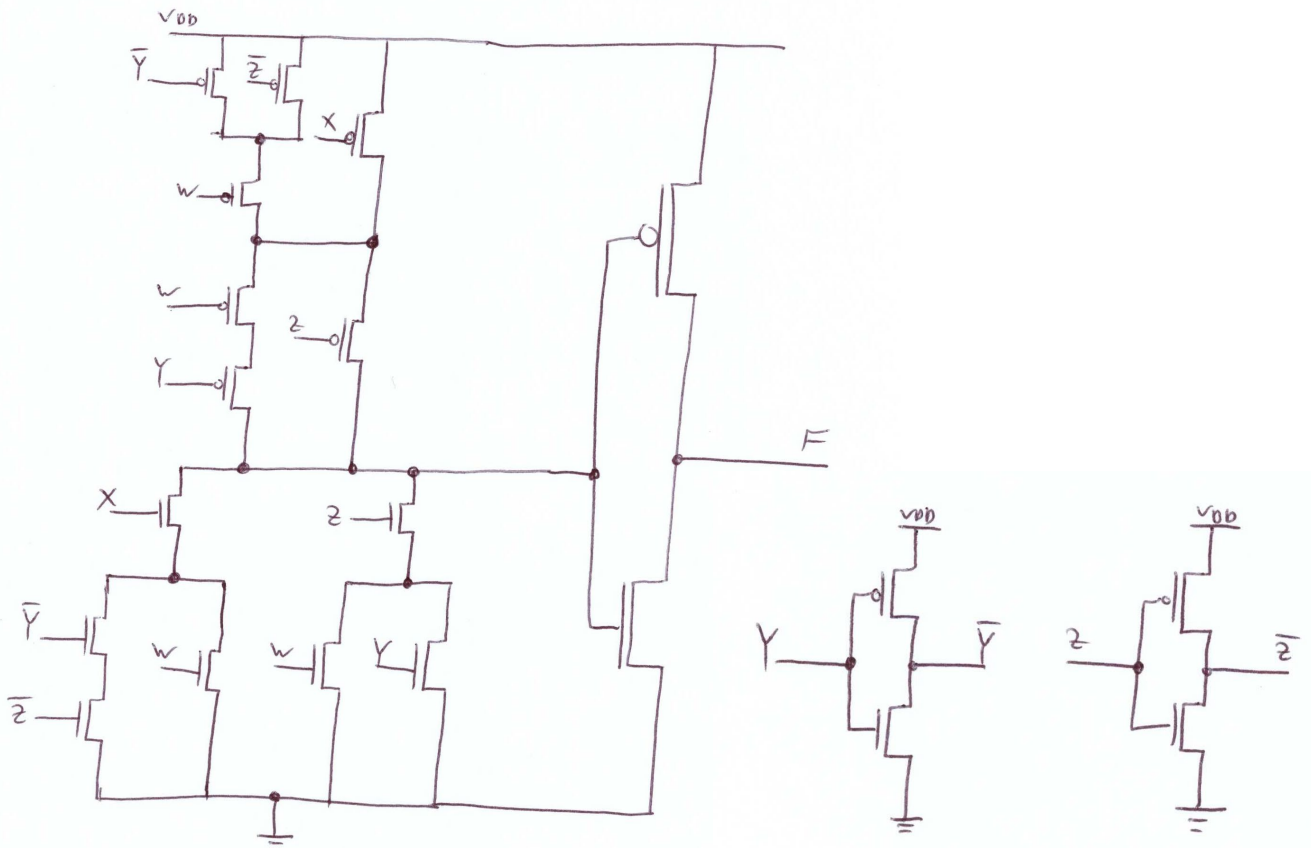
$$F = wX + wZ + YZ + X\bar{Y}\bar{Z} \quad (24)$$

$$= X(w + \bar{Y}\bar{Z}) + Z(w + Y) \quad (20)$$

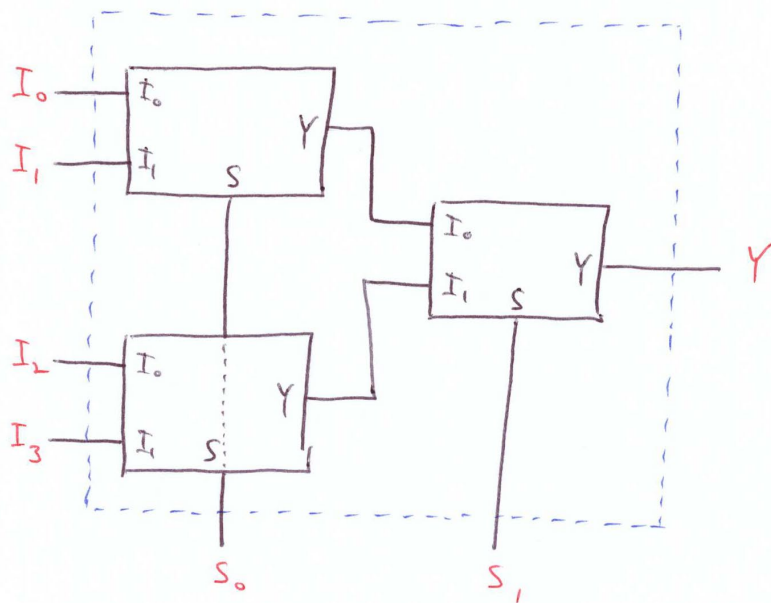
$$\bar{F} = \bar{X}\bar{Z} + \bar{w}Y\bar{Z} + \bar{w}\bar{Y}Z \quad (24)$$

$$= \bar{X}\bar{Z} + \bar{w}(Y\bar{Z} + \bar{Y}Z) \quad (22)$$

Implement: $F = X(w + \bar{Y}\bar{Z}) + Z(w + Y)$



11. A 4-to-1-Line Multiplexer can be implemented by cascading three 2-to-1 MUX in the following manner:



Each of the 2-to-1 MUX can be implemented using inverters and transmission gates.

